

FEATURES

- 4.90–5.30GHz Bandwidth
- Input/Output Impedance Matched to 50 Ohms
- +39.5 dBm Output Power at 1dB Compression
- 10.5 dB Power Gain at 1dB Compression
- 35% Power Added Efficiency
- -46 dBc IM3 at PO = 28.5 dBm SCL
- 100% Tested for DC, RF, and R_{TH}



ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)



Caution! ESD sensitive device.

SYMBOL	PARAMETERS/TEST CONDITIONS ¹	MIN	TYP	MAX	UNITS
P_{1dB}	Output Power at 1dB Compression $f = 4.90\text{-}5.30\text{GHz}$ $V_{DS} = 10\text{ V}, I_{DSQ} \approx 2200\text{mA}$	38.5	39.5		dBm
G_{1dB}	Gain at 1dB Compression $f = 4.90\text{-}5.30\text{GHz}$ $V_{DS} = 10\text{ V}, I_{DSQ} \approx 2200\text{mA}$	9.5	10.5		dB
ΔG	Gain Flatness $f = 4.90\text{-}5.30\text{GHz}$ $V_{DS} = 10\text{ V}, I_{DSQ} \approx 2200\text{mA}$			± 0.6	dB
PAE	Power Added Efficiency at 1dB Compression $V_{DS} = 10\text{ V}, I_{DSQ} \approx 2200\text{mA}$ $f = 4.90\text{-}5.30\text{GHz}$		35		%
I_{d1dB}	Drain Current at 1dB Compression $f = 4.90\text{-}5.30\text{GHz}$		2300	2600	mA
IM3	Output 3rd Order Intermodulation Distortion $\Delta f = 10\text{MHz}$ 2-Tone Test. $P_{out} = 28.5\text{ dBm S.C.L.}$ $V_{DS} = 10\text{ V}, I_{DSQ} \approx 65\% I_{DSS}$ $f = 5.30\text{GHz}$	-43	-46		dBc
I_{DSS}	Saturated Drain Current $V_{DS} = 3\text{ V}, V_{GS} = 0\text{ V}$		4000	5000	mA
V_P	Pinch-off Voltage $V_{DS} = 3\text{ V}, I_{DS} = 40\text{ mA}$		-2.5	-4.0	V
R_{TH}	Thermal Resistance ³		3.5	4.0	$^\circ\text{C/W}$

Note: 1. Tested with 100 Ohm gate resistor. 2. S.C.L. = Single Carrier Level. 3. Overall R_{th} depends on case mounting.

ABSOLUTE MAXIMUM RATING^{1,2}

SYMBOLS	PARAMETERS	ABSOLUTE ¹	CONTINUOUS ²
V_{DS}	Drain-Source Voltage	15	10V
V_{GS}	Gate-Source Voltage	-5	-4.5V
I_{gsf}	Forward Gate Current	86.4mA	28.8mA
I_{gsr}	Reverse Gate Current	-14.4mA	-4.8mA
P_{in}	Input Power	38.5dBm	@ 3dB Compression
T_{ch}	Channel Temperature	175 $^\circ\text{C}$	175 $^\circ\text{C}$
T_{stg}	Storage Temperature	-65 to +175 $^\circ\text{C}$	-65 to +175 $^\circ\text{C}$
P_t	Total Power Dissipation	38W	38W

Note: 1. Exceeding any of the above ratings may result in permanent damage.

2. Exceeding any of the above ratings may reduce MTTF below design goals.

Specifications are subject to change without notice.

Excelics Semiconductor, Inc. 310 De Guigne Drive, Sunnyvale, CA 94085

Phone: 408-737-1711 Fax: 408-737-1868 Web: www.excelics.com

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Revised February 2008



EIC4953-8

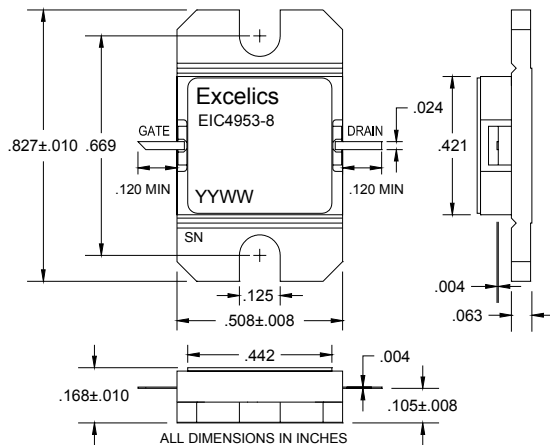
ISSUED 02/28/2008

4.90-5.30 GHz 8-Watt Internally Matched Power FET

PACKAGES OUTLINE

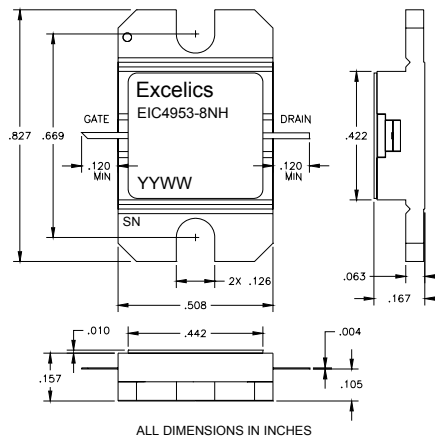
Dimensions in inches, Tolerance $\pm .005$ unless otherwise specified

EIC4953-8 (Hermetic)



Caution! ESD sensitive device.

EIC4953-8NH (Non-Hermetic)



Caution! ESD sensitive device.

ORDERING INFORMATION

Part Number	Packages	Grade ¹	f _{Test} (GHz)	P _{1dB} (min)	IM ₃ (min) ²
EIC4953-8	Hermetic	Industrial	4.90-5.30GHz	38.5	-43
EIC4953-8NH	Non-Hermetic	Industrial	4.90-5.30GHz	38.5	-43

Notes: 1. Contact factory for military and hi-rel grades.
2. Exact test conditions are specified in "Electrical Characteristics" table.

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